

A Product Line of Diodes Incorporated



Small Plastic Package, Dual SPDT Analog Switch

Features

- → CMOS Technology for Bus and Analog Applications
- → Low On-Resistance: 0.45Ω
- → Wide V_{DD} Range: 1.8V to 4.2V
- → Rail-to-Rail Signal Range
- → High Off Isolation: -83dB @ 100kHz
- ➔ Crosstalk Rejection Reduces Signal Distortion: -108dB @ 100kHz
- → Break-Before-Make Switching
- ➔ Extended Industrial Temperature Range: -40°C to 85°C
- → ESD protection : 4kV(HBM)
 - Packaging (Pb-free & Green):
 - -10-pin UQFN (ZM), 1.4mm x 1.8mm

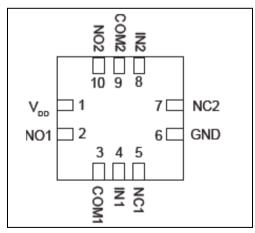
Applications

- → Cell Phones
- → PDAs

→

- → MP3 Players
- ➔ Portable Instrumentation
- ➔ Computer Peripherals
- ➔ Speaker Headset Switching
- → Power Routing
- ➔ Relay Replacement
- → Audio and Video Signal Routing
- → PCMCIA Cards
- ➔ Modems

Pin Configuration (Top view)

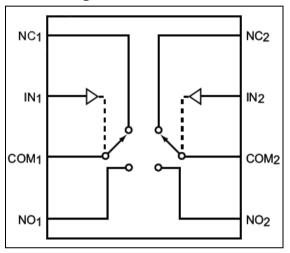


Description

PI3A223 is a dual fast single-pole double throw (SPDT) CMOS switch. It can be used as an analog switch or as a lowdelay bus switch. Specified over a wide operating power supply voltage, 1.8V to 4.2V, the PI3A223 has an On-Resistance of 0.45Ω at +4.2V.

Break-before-make switching prevents both switches being enabled simultaneously. This eliminates signal disruption during switching.

Block Diagram



Pin Description

Pin#	Name	Description
1	V _{DD}	Positive Power Supply
2	NO1	Data Port (Normally open)
3	COM1	Common Output / Data Port
4	IN1	Logic Control
5	NC1	Data Port (Normally closed)
6	GND	Ground
7	NC2	Data Port (Normally closed)
8	IN2	Logic Control
9	COM2	Common Output / Data Port
10	NO2	Data Port (Normally open)

Function Table

L	ogic Input (IN _X)	Function
	0	NC _X Connected to COM _X
	1	NO _X Connected to COM _X
	1	

Note: x = 1 or 2





Maximum Ratings

Storage Temperature	65°C to +150°C
Ambient Temperature with Power Applied	40°C to +85°C
Supply Voltage V _{DD}	0.5Vto +4.6V
Control Input Voltage V _{INx}	0Vto +4.6V
DC Input Voltage V _{INPUT}	0.5Vto +4.6V
Continuous Current NO_NC_COM	±300mA
Peak Current NO_NC_COM_	
(pulsed at 1ms 50% duty cycle)	±400mA
Peak Current NO_NC_COM_	
(pulsed at 1ms 10% duty cycle)	±500mA
ESD(HBM)	4kV

Note:

Stresses greater than those listed under MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

The input and output negative voltage ratings may be exceeded if the input and output diode current ratings are observed.

Control input must be held HIGH or LOW; it must not float.

Recommended Operating Conditions

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
V _{DD}	Operating Voltage	-	1.8	-	4.2	V
V _{IN}	Control Input Voltage	-	0	-	V _{DD}	V
V _{INPUT}	Switch Input Voltage	-	-0.3	-	4.2	V
T _A	Operating Temperature	-	-40	25	85	°C
t _r , t _f	Input Rise and Fall Time	-	0	-	10	ns/V

DC Electrical Characteristics

+3.0V Supply (V_{DD} = 2.7V to 3.6V, V_{IH} =+1.6V, V_{IL} =+0.4V, T_A = -40°C to 85°C, unless otherwise noted. Typical values are at 3.0V and +25°C.)

Parameter	Symbol	ymbol Test Conditions		Min.	Тур.	Max.	Units	
ANALOG SWITCH								
Analog Signal Range	V _{NO} , V _{NC} , V _{COM}	-	-40 °C to 85 °C	0	-	V_{DD}	v	
On-Resistance	R _{ON}	$V_{DD} = 2.7V, I_{COM} = 100mA, V_{NO} \text{ or}$ $V_{NC} = 1V, Test Circuit 1$	+25°C -40 °C to 85 °C	-	0.55	0.9	Ω	
On-Resistance Match Between Channels	ΔR _{ON}	$V_{DD} = 2.7V, I_{COM} = 100mA, V_{NO} \text{ or}$ $V_{NC} = 1V, Test Circuit 1$	+25°C -40 °C to 85 °C	-	0.05	0.22	Ω	
On-Resistance	R _{ONF}	$V_{DD} = 2.7V$, $I_{COM} = 100mA$, V_{NO} or	+25°C	-	0.1	0.22	Ω	
Flatness Source Off	I _{OFF (NO)} or	$V_{\text{NC}} = 1V, 2.5V, Test Circuit 1$ $V_{\text{DD}} = 3.6V, V_{\text{NO}} \text{ or } V_{\text{NC}} = 2.2V/2.2V$	-40 °C to 85 °C -40 °C to 85 °C	-	0.1	0.26		
Leakage Current Channel On Leakage Current	I _{OFF (NC)} I _{NC(ON)} , I _{NO(ON)} , I _{COM} (ON)	$\begin{array}{l} 3.3V/0.3V, V_{COM} = 0.3V/3.3V \\ V_{DD} = 3.6V, V_{NO} \mbox{ or } V_{NC} = 3V/ \\ 0.3V, V_{COM} = 3V/0.3V, \mbox{ or floating} \end{array}$	-40 °C to 85 °C	-	-	1	μA	
DIGITAL INPUTS								
Input Logic High	V _{IH}	-	-40 °C to 85 °C	1.2	-	-	v	
Input Logic Low	V _{IL}	-	-40 °C to 85 °C	-	-	0.5	v	
IN Input Leakage Current	I_{IN}	$V_{DD} = 2.7V, V_{IN} = 0 \text{ or } 2.7V$	-40 °C to 85 °C	-	-	1	μΑ	
DYNAMIC CHARA	DYNAMIC CHARACTERISTICS							
Turn-On Time	t _{ON}	$V_{IH}=1.5V, V_{IL}=0V,$ See Test Circuit Figure 2.	+25°C	-	16	-	ns	
Turn-Off Time	t _{OFF}	V_{IH} =1.5V, V_{IL} =0V, See Test Circuit Figure 2.	+25°C	-	60	-	ns	
Break-Before-Make	t _D	$V_{IH} = 1.5V, V_{IL} = 0V,$	+25°C	-	10	-	ns	



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PI3A223

Parameter	Symbol	Test Conditions		TEMP	Min.	Тур.	Max.	Units
Delay		See Test Circuit Figure 3.						
		V _{BIAS} =1.5V, V _{IN} =0dBm,	100kHz	+25°C	-	-81	-	
COM-NC/NO and NC-NO Isolations	O _{ISO}	V_{IH} =1.5V, V_{IL} =0V. See Test Circuit Figure 4 &	1MHz	+25°C	-	-61	-	dB
		Figure 5.	10MHz	+25°C	-	-39	-	
		$V_{BIAS} = 1.5V,$	100kHz	+25°C	-	-108	-	
Channel-to-Channel X _{TALKD} Crosstalk	X_{TALKD}	V_{DD} =0dBm, V_{IH} =1.5V, V_{IL} =0V See Test Circuit Figure 6.	1MHz	+25°C	-	-110	-	dB
			10MHz	+25°C	-	-90	-	
3dB Bandwidth	$f_{\rm 3dB}$	$V_{BIAS} = 1.5V, V_{IN}=0dBm,$ $V_{IH}=1.5V, V_{IL}=0V.$ See Test Circuit Figure 7.		+25°C	-	79	-	MHz
Charge Injection Select Input to Common I/O	Q	$V_{IN} = GND, R_S = 0, C_L = 1nF,$ $V_{IH}=1.5V, V_{IL}=0V$ See Test Circuit Figure 8.		+25°C	-	35	-	pC

+4.2V Supply ($V_{DD} = 4.2V$, $T_A = -40$ °C to 85 °C, unless otherwise noted. Typical values are at 4.2V and +25 °C.)

Parameter	Symbol	Test Conditions		TEMP	Min.	Тур.	Max.	Units
ANALOG SWITCH	· · · ·			·				
Analog Signal Range	V _{NO} , V _{NC} , V _{COM}	-		-40 °C to 85 °C	0	-	V_{DD}	V
On-Resistance	R _{ON}	$V_{DD} = 4.2V, I_{COM} = 100m.$ $V_{NC} = 1V, Test Circuit 1$	A, V_{NO} or	+25°C -40 °C to 85 °C	-	0.45	0.75 0.85	Ω
On-Resistance Match Between Channels	ΔR _{ON}	$V_{DD} = 4.2V, I_{COM} = 100m.$ $V_{NC} = 1V, Test Circuit 1$	A, V _{NO} or	+25 °C -40 °C to 85 °C	-	0.05	0.18	Ω
On-Resistance Flatness	R _{ONF}	$V_{DD} = 4.2V, I_{COM} = 100m.$ $V_{NC} = 1V, 2.5V, Test Circ$		+25 °C -40 °C to 85 °C	-	0.1	0.22	Ω
Source Off Leakage Current	$I_{OFF (NO)} \text{ or } \\ I_{OFF (NC)}$	V_{DD} = 4.2V, V_{NO} or 3.3V/0.3V, V_{COM} = 0.3V/3	V _{NC} =	-40 °C to 85 °C	-	-	1	4
Channel On Leakage Current	$I_{\rm NC(ON)},$ $I_{\rm NO(ON)}, I_{\rm COM}$ (ON)	$V_{DD} = 4.2V, V_{NO} \text{ or } V_{NC} = 3V/$ 0.3V, V _{CO} M = 3V/0.3V, or floating		-40 °C to 85 °C	-	-	1	μA
DIGITAL INPUTS								
Input Logic High	V _{IH}	-		-40 °C to 85 °C	1.2	-	-	v
Input Logic Low	V _{IL}	-		-40 °C to 85 °C	-	-	0.5	v
IN Input Leakage Current	I _{IN}	$V_{DD} = 4.2V, V_{IN} = 0 \text{ or } 4.2V$		-40 °C to 85 °C	-	-	1	μΑ
DYNAMIC CHARA	CTERISTICS	·		•	•	•		•
Turn-On Time	t _{ON}	V _{IH} =3V, V _{IL} =0V, See Test Circuit Figure 2.		+25°C	-	13	-	ns
Turn-Off Time	t _{OFF}	V _{IH} =3V, V _{IL} =0V, See Test Circuit Figure 2.		+25°C	-	38	-	ns
Break-Before-Make Delay	t _D	V _{IH} =3V, V _{IL} =0V, See Test Circuit Figure 3.		+25°C	-	8	-	ns
		$V_{BIAS} = 2.1 V,$	100kHz	+25°C	-	-83	-	
COM-NC/NO and NC-NO Isolations	O _{ISO}	V _{IN} =0dBm, V _{IH} =3V, V _{IL} =0V. See Test Circuit	1MHz	+25°C	-	-61	-	dB
		Figure 4 & Figure 5.	10MHz	+25°C	-	-39	-	
Channel-to-channel	X _{TALK}	$V_{BIAS} = 2.1V,$ $V_{IN}=0dBm, V_{IH}=3V,$	100kHz	+25°C	-	-108	-	dB
Crosstalk		V _{IL} =0V See Test Circuit	1MHz	+25°C	-	-110	-	



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Parameter	Symbol	Test Conditions	Test Conditions		Min.	Тур.	Max.	Units
		Figure 6.	10MHz	+25°C	-	-90	-	
3dB Bandwidth	\mathbf{f}_{3dB}	$V_{BIAS} = 2.1V, V_{IN}=0dBm, V_{IH}=3V, V_{IL}=0V.$ See Test Circuit Figure 7.		+25°C	-	84	-	MHz
Charge Injection Select Input to Common I/O	Q	$V_{IN} = GND, R_S = 0, C_L = 1nF,$ $V_{IH}=3V, V_{IL}=0V$ See Test Circuit Figure 8.		+25°C	-	50	-	pC
POWER REQUIREM	1ENTS							
Power Supply Range	V _{DD}	-		-40 °C to 85 °C	1.8	-	4.2	V
Power Supply Current	I _{CC}	V_{DD} =4.2V, V_{IN} =0V or V_{DD})	-40 °C to 85 °C	-	-	1	μΑ

Capacitance

Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Units
NC Off Capacitance	C _{NC (OFF)}	f = 1MHz, See Test Circuit Figure 9.	-	20	-	
NO Off Capacitance	C _{NO (OFF)}	f = 1MHz, See Test Circuit Figure 9.	-	20	-	πE
NC On Capacitance	C _{NC (ON)}	f = 1MHz, See Test Circuit Figure 10.	-	55	-	pF
NO On Capacitance	C _{NO (ON)}	f = 1MHz, See Test Circuit Figure 10.	-	55	-	





Test Circuits and Timing Diagrams

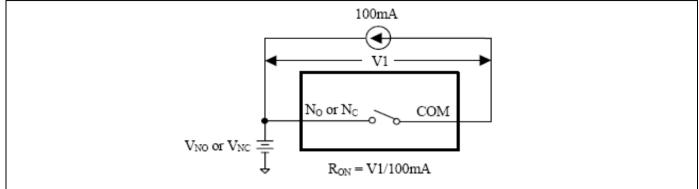


Figure 1. On Resistance

Notes:

1. Unused input (NC or NO) must be grounded.

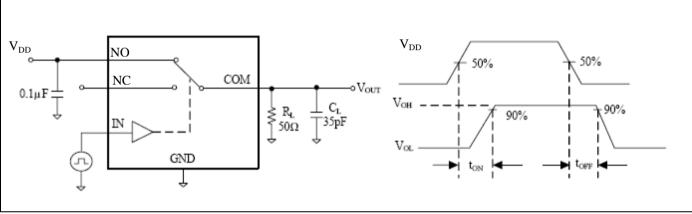


Figure 2. Switching Times

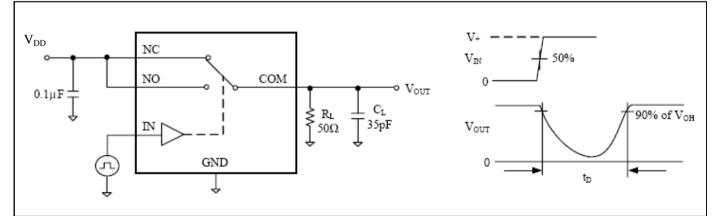


Figure 3. Break Before Make Interval Timing



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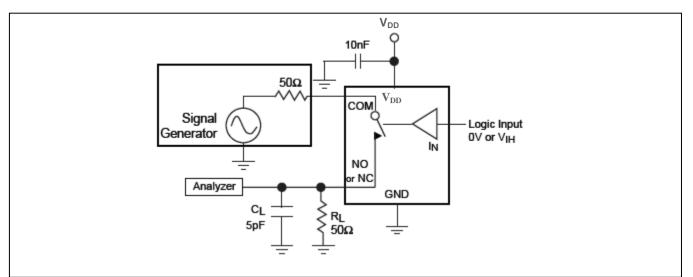


Figure 4. COM-NC/NO Isolation

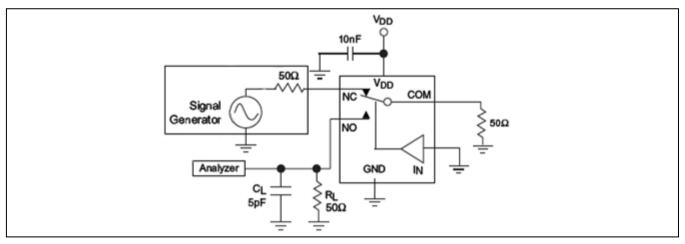


Figure 5. NC-NO Isolation





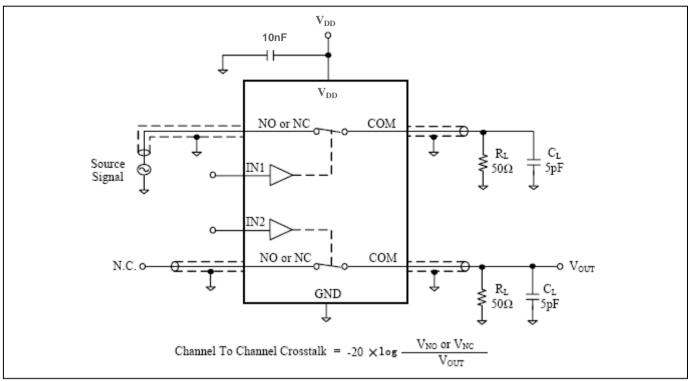
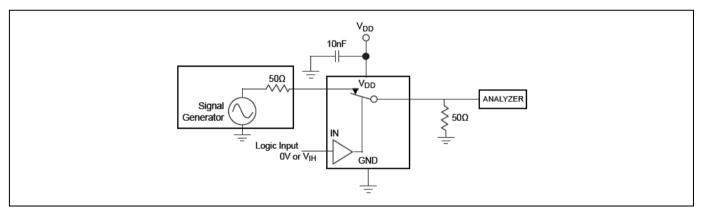


Figure 6. Channel-to-Channel Crosstalk





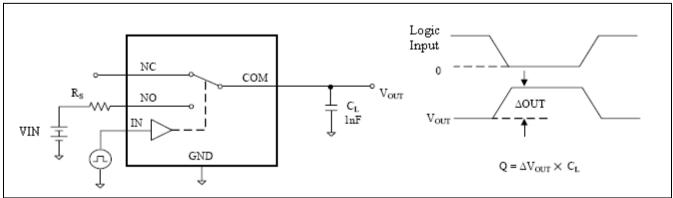


Figure 8. Charge Injection





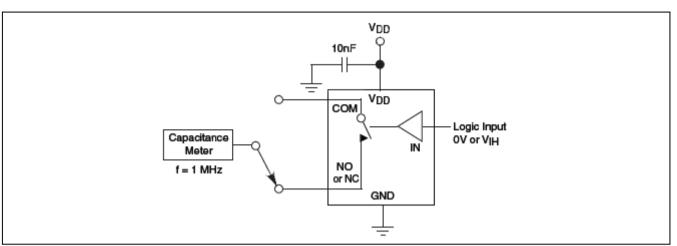


Figure 9. Channel Off Capacitance

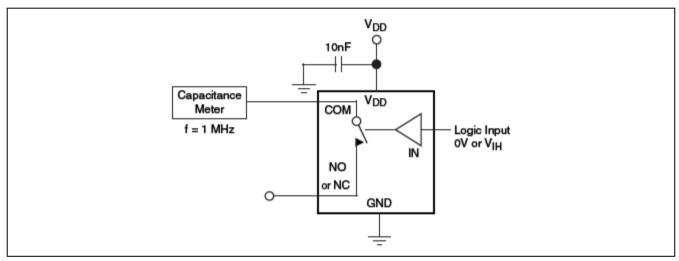
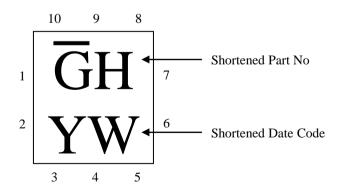


Figure 10. Channel On Capacitance

Part Marking

ZM Package

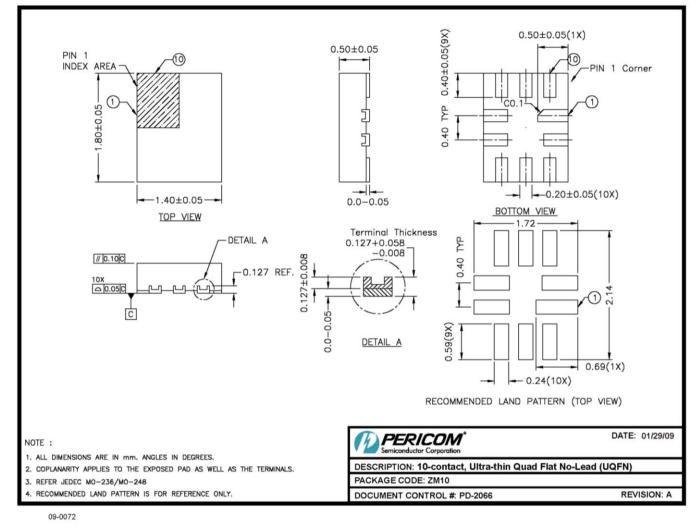






Packaging Mechanical

10-UQFN (ZM)



For latest package info.

please check: http://www.diodes.com/design/support/packaging/pericom-packaging/packaging-mechanicals-and-thermal-characteristics/

Ordering Information

Part Number	Packaging Code	Package Description
PI3A223ZMEX	ZM	10-Contact, Ultra-thin Quad Flat No-Lead (UQFN)

Notes:

• EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.

• See http://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

• Thermal characteristics can be found on the company web site at www.diodes.com/design/support/packaging/

• E = Pb-free and Green

• X suffix = Tape/Reel





PI3A223

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